

IN THE CLAIMS:

All of the claims that remain pending and under consideration in the above-referenced application are reproduced below, in clean form, for the sake of clarity.

Please enter the claims as follows:

1. (Amended) A method for establishing an electrical contact with at least one semiconductor device, comprising:  
establishing an electrical contact between a first member of an electrical connector and a contact that is in electrical communication with the at least one semiconductor device; and magnetically drawing at least one of said first member [toward] and said contact toward the other of said first member and said contact.
2. (Amended) The method of claim 1, wherein said magnetically drawing is effected in a direction substantially normal to a plane of said contact.
3. (Amended) The method of claim 1, wherein said magnetically drawing is effected in a direction substantially normal to a plane of a substrate upon which said contact is carried.
4. (Amended) The method of claim 1, wherein said magnetically drawing is effected by positioning a second member of said electrical connector opposite said first member.
5. (Amended) The method of claim 4, wherein said magnetically drawing is effected by magnetically attracting at least one of said first member and said second member toward at least the other of said first member and said second member.
6. (Amended) The method of claim 4, wherein said magnetically drawing comprises securing said first and second members to a substrate upon which said contact is carried.

7. (Amended) The method of claim 1, wherein said magnetically drawing comprises magnetically [attracting] securing said first member [against] to said contact.

8. (Amended) A method for stress testing a plurality of semiconductor devices carried upon a common substrate and in communication with common ground and power contacts, comprising:  
establishing electrical contact between a first member of an electrical connector and at least one contact of the ground contact and the power contact; and  
magnetically drawing at least one of said first member [toward] and said at least one contact toward the other of said first member and said at least one contact.

9. (Twice amended) The method of claim 8, wherein said magnetically drawing is effected in a direction substantially normal to a plane of the common substrate.

10. (Twice amended) The method of claim 8, wherein said magnetically drawing nonrigidly biases said first member against said at least one contact.

11. (Amended) The method of claim 8, wherein said magnetically drawing comprises positioning a second member of said electrical connector opposite the substrate from said first member.

12. The method of claim 11, wherein at least one of said first member and said second member is drawn toward at least the other of said first member and said second member.

13. (Amended) The method of claim 12, wherein said magnetically drawing comprises magnetically attracting at least one of said first member and said second member toward at least the other of said first member and said second member.

14. (Amended) The method of claim 8, wherein said magnetically drawing comprises magnetically [attracting] securing said first member [against] to said at least one contact.

15. (Amended) The method of claim 8, wherein said magnetically drawing comprises securing at least said first member in position relative to the substrate.

16. (Amended) The method of claim 8, further comprising:  
electrically connecting another first member of another electrical connector to another of the  
ground contact and the power contact; and  
magnetically drawing said another first member toward said another contact.

17. The method of claim 16, further comprising:  
applying a substantially constant amount of current to each semiconductor device of the plurality  
of semiconductor devices through said first member and said another first member.

18. The method of claim 17, further comprising:  
heating each of the plurality of semiconductor devices.

19. The method of claim 18, wherein said heating comprises cycling a temperature of  
each of the plurality of semiconductor devices.

20. The method of claim 18, wherein said heating comprises varying a temperature of  
each of the plurality of semiconductor devices.